



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



企业QQ二维码

## Features

- $BV_{CEO} > -150V$
- $I_C = -600mA$  high Collector Current
- Ideal for Medium Power Switching or Amplification Applications
- Complementary PNP Type: NK-DZT5551

## Mechanical Data

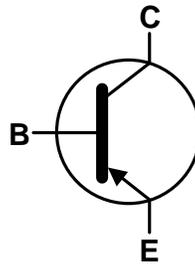
- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight: 0.112 grams (Approximate)

## Applications

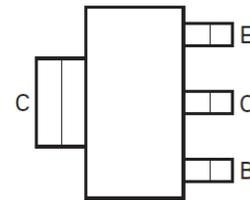
- Amplifiers
- Power Supplies



Top View



Device Symbol



Top View  
Pin-Out

### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-160	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-150	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Collector Current	I <sub>C</sub>	-600	mA

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation @T <sub>A</sub> = +25°C	P <sub>D</sub>	1	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C	R <sub>θJA</sub>	125	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

### ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the collector lead on minimum recommended pad (MRP) layout 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

### Thermal Characteristics and Derating Information

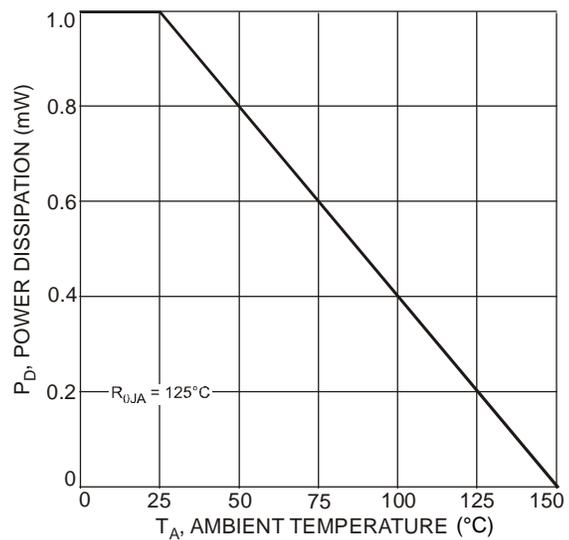


Fig. 1 Max Power Dissipation vs. Ambient Temperature

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Collector-Base Breakdown Voltage	$BV_{CBO}$	-160	—	—	V	$I_C = -100\mu\text{A}$ , $I_E = 0$
Collector-Emitter Breakdown Voltage (Note 7)	$BV_{CEO}$	-150	—	—	V	$I_C = -1\text{mA}$ , $I_B = 0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-6	—	—	V	$I_E = -10\mu\text{A}$ , $I_C = 0$
Collector-Base Cut-off Current	$I_{CBO}$	—	—	-50	nA	$V_{CB} = -120\text{V}$ , $I_E = 0$
Emitter-Base Cut-off Current	$I_{EBO}$	—	—	-50	nA	$V_{EB} = -3\text{V}$ , $I_C = 0$
<b>ON CHARACTERISTICS (Note 7)</b>						
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	—	-0.2 -0.5	V	$I_C = -10\text{mA}$ , $I_B = -1\text{mA}$ $I_C = -50\text{mA}$ , $I_B = -5\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	—	-1.0	V	$I_C = -10\text{mA}$ , $I_B = -1\text{mA}$ $I_C = -50\text{mA}$ , $I_B = -5\text{mA}$
Static Forward Current Transfer Ratio	$h_{FE}$	50 60 50	— — —	— 240 —	—	$I_C = -1\text{mA}$ , $V_{CE} = -5\text{V}$ $I_C = -10\text{mA}$ , $V_{CE} = -5\text{V}$ $I_C = -50\text{mA}$ , $V_{CE} = -5\text{V}$
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Transition Frequency	$f_T$	100	—	300	MHz	$V_{CE} = -10\text{V}$ , $I_C = -10\text{mA}$ , $f = 100\text{MHz}$
Output Capacitance	$C_{obo}$	—	—	6	pF	$V_{CB} = -10\text{V}$ , $f = 1\text{MHz}$ , $I_E = 0$
Small Signal Current Gain	$h_{FE}$	40	—	260	—	$V_{CE} = -10\text{V}$ , $I_C = -1.0\text{mA}$ , $f = 1.0\text{kHz}$
Noise Figure	NF	—	—	8	dB	$V_{CE} = -5.0\text{V}$ , $I_C = -200\mu\text{A}$ , $R_S = 10\Omega$ , $f = 1.0\text{kHz}$

Note: 7. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ . Duty cycle  $\leq 2\%$ .

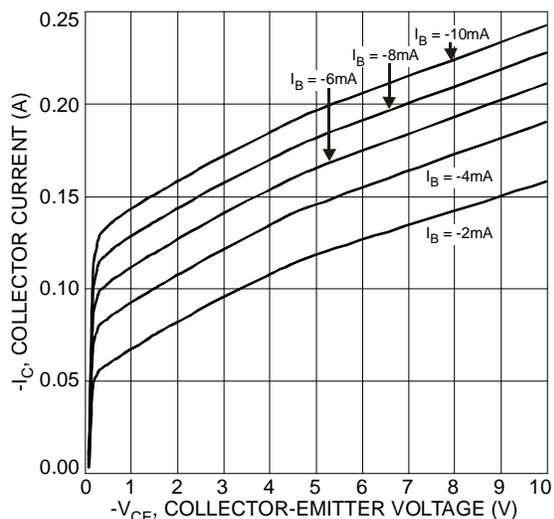
**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

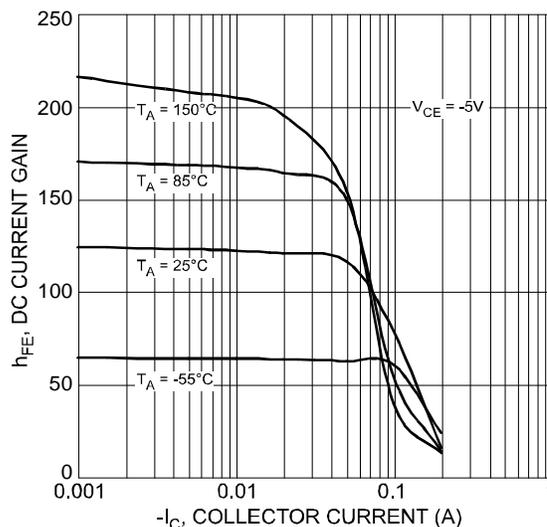


Fig. 3 Typical DC Current Gain vs. Collector Current

Typical Electrical Characteristics (Cont.)

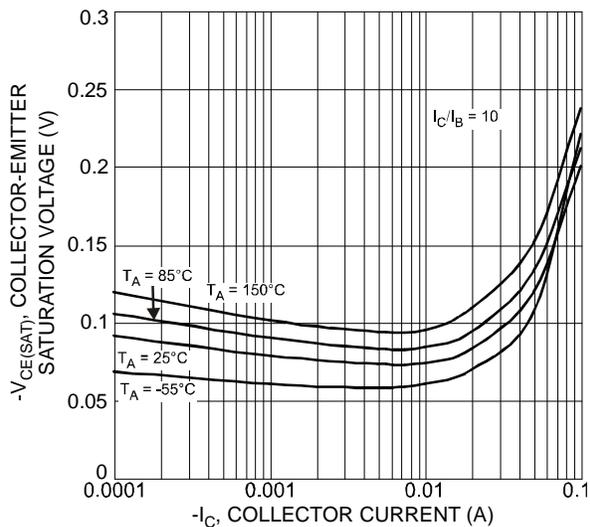


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

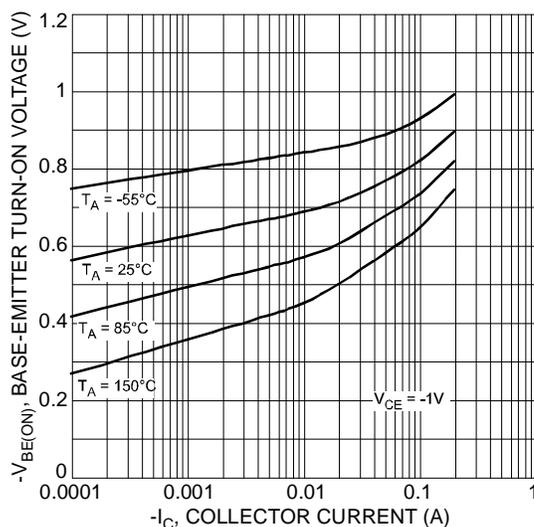


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

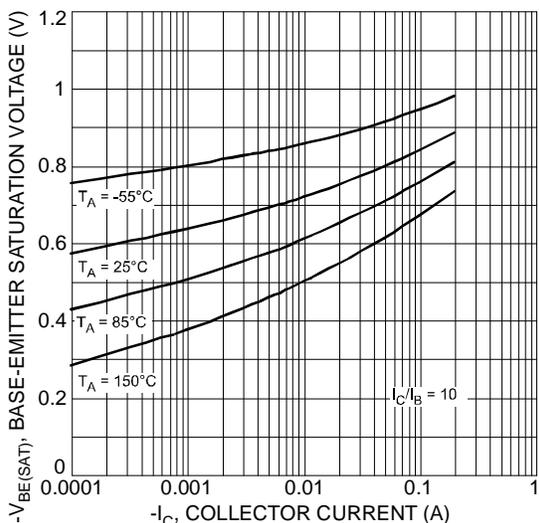


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

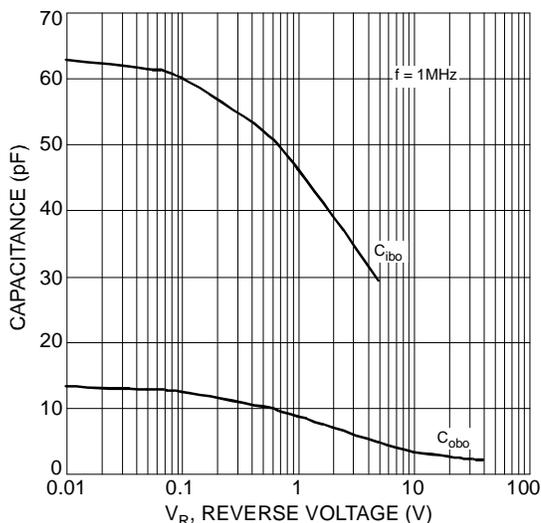


Fig. 7 Typical Capacitance Characteristics

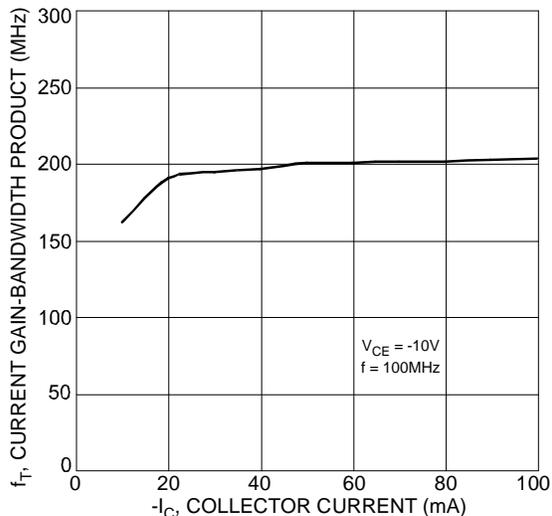
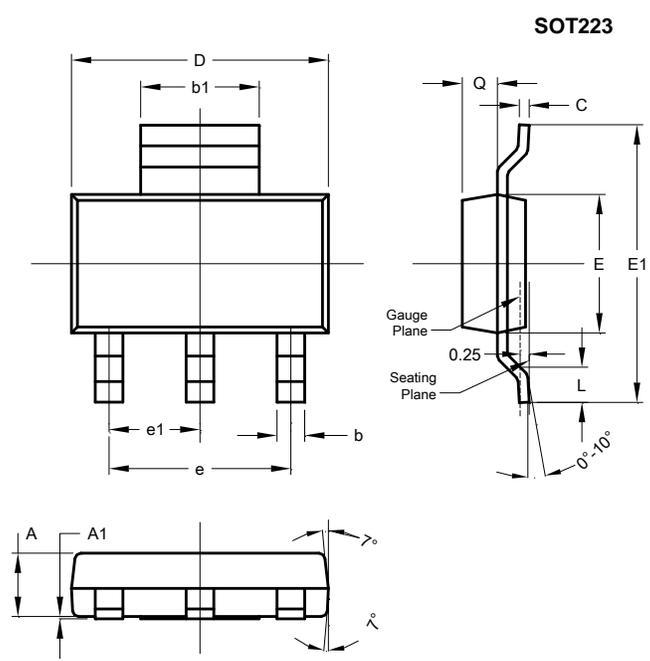


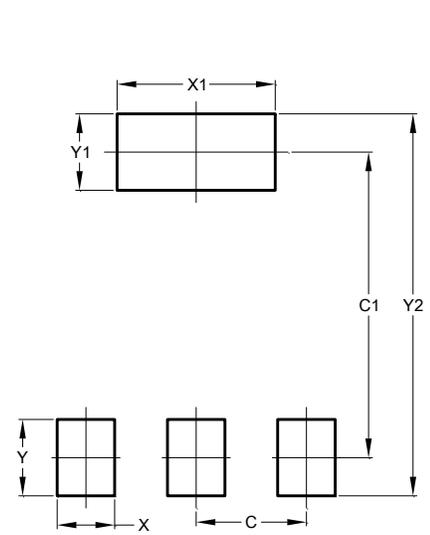
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

### Package Outline Dimensions



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

### Suggested Pad Layout



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00